

UTC UNISONIC TECHNOLOGIES CO., LTD

MGBR40V45C

Preliminary

DIODE

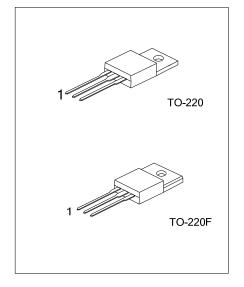
DUAL MOS GATED BARRIER RECTIFIER

DESCRIPTION

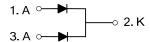
The UTC MGBR40V45C is a dual mos gated barrier rectifiers, it uses UTC's advanced technology to provide customers with low forward voltage drop and high switching speed, etc.

FEATURES

- * Very low forward voltage drop
- * High switching speed



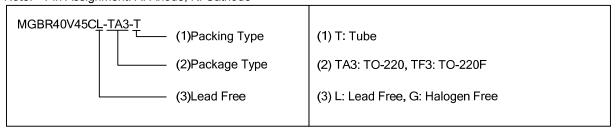
SYMBOL



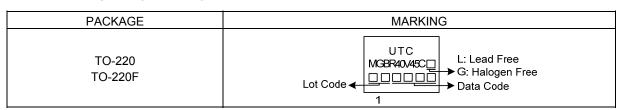
ORDERING INFORMATION

Ordering Number		Dackage	Pin Assignment			Daakina	
Lead Free	Halogen Free	Package	1	2	3	Packing	
MGBR40V45CL-TA3-T	MGBR40V45CG-TA3-T	TO-220	Α	K	Α	Tube	
MGBR40V45CL-TF3-T	MGBR40V45CG-TF3-T	TO-220F	Α	K	Α	Tube	

Note: Pin Assignment: A: Anode, K: Cathode



MARKING INFORMATION



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■ ABSOLUTE MAXIMUM RATINGS (PER LEG) (T_A=25°C unless otherwise specified)

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitance load, derate current by 20%.

PARAMETER	SYMBOL	RATINGS	UNIT
DC Blocking Voltage	V_{RM}	45	V
Working Peak Reverse Voltage	V_{RWM}	45	V
Peak Repetitive Reverse Voltage	V_{RRM}	45	V
Average Restified Output Current Per Device Per Le		20	Α
Average Rectified Output Current Per Device Total	Io	40	Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	I _{FSM}	280	Α
Operating Junction Temperature	TJ	-65~+150	°C
Storage Temperature	T _{STG}	-65~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL CHARACTERISTICS (PER LEG)

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Case	θ_{JC}	2	°C/W

■ ELECTRICAL CHARACTERISTICS (PER LEG) (T_A =25°C unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Reverse Breakdown Voltage (Note 1)	V _{(BR)R}	I _R =0.50mA	45			V
Farmed Valtage Days	I VEM	I _F =20A, T _J =25°C			0.55	٧
Forward Voltage Drop		I _F =20A, T _J =125°C			0.50	V
Leakage Current (Note 1)	I I I I I I I I I I I I I I I I I I I	V _R =45V, T _J =25°C			500	μΑ
		V _R =45V, T _J =125°C			100	mΑ

Notes: 1. Short duration pulse test used to minimize self-heating effect.

^{2.} Thermal resistance junction to case mounted on heatsink.

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DIODE